

RECEIVED
CENTRAL FAX CENTER

APR 10 2008

Customer No.: 31561
Docket No.: 13794-US-PA
Application No.: 10/711,160AMENDMENTTo the Specification

[Para 16] On the other hand, the transparent end portions 210a of the isolated line patterns 210 and the transparent phase-shift region 230 may be recessed portions of the substrate 200, wherein the ~~0-shift~~ π -shift end portion 210a of an isolated line pattern 210 is ~~recess~~ recessed more than the ~~0/2-shift~~ $\pi/2$ -shift region 230.

[Para 20] It is noted that though the line patterns are arranged in pairs in an end-to-end manner within the above embodiment, a single isolated line pattern having a transparent ~~0-shift~~ π -shift end portion, or a single group of dense line patterns with a transparent ~~0/2-shift~~ $\pi/2$ -shift region adjacent to their ends, can also reduce the LES effect. Moreover, this invention not only is applicable to a photomask with isolated/dense line patterns thereon as in the above embodiment, but also can be applied to a photomask with other[[type]] types of isolated/dense linear patterns thereon. In addition, the photomask of this invention may include merely isolated line patterns each having a transparent ~~0-shift~~ π -shift end portion, or merely dense line patterns with a transparent ~~0/2-shift~~ $\pi/2$ -shift region adjacent to their ends.